

TRANSISTOR (NPN)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM}: 1W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: 1.5A$$

Collector-base voltage

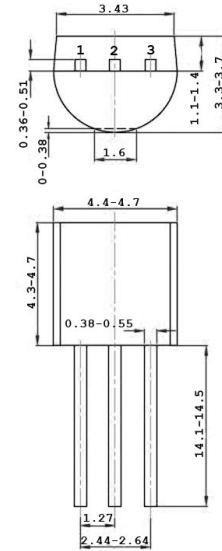
$$V_{(BR)CBO}: 40V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

TO-92

1. EMITTER
2. BASE
3. COLLECTOR



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100 \mu A, I_E=0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1mA, I_B=0$	25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100 \mu A, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	85	300	
	$h_{FE(2)}$	$V_{CE}=1V, I_C=800mA$	40		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=800mA, I_B=80mA$		0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=800mA, I_B=80mA$		1.2	V
Base-emitter voltage	V_{BE}	$I_E=1.5A$		1.6	V
Transition frequency	f_r	$V_{CE}=10V, I_C=50mA$ $f=30MHz$	190		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	85-160	120-200	160-300